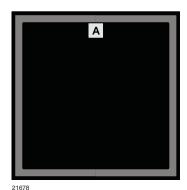


Vishay Semiconductors

Silicon PIN Photodiode



DESCRIPTION

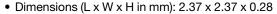
GENERAL INFORMATION

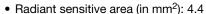
T1120P is a high speed and high sensitive PIN photodiode chip with 4.4 mm² sensitive area detecting visible and near infrared radiation. Anode is the bond pad on top.

FEATURES

· Package type: chip







· High photo sensitivity

· High radiant sensitivity

- · Suitable for visible and near infrared radiation
- Fast response times
- Angle of half sensitivity: $\varphi = \pm 60^{\circ}$
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC



· High speed photo detector

The datasheet is based on Vishay optoelectronics sample testing under certain predetermined and assumed conditions, and is provided for illustration purpose only. Customers are encouraged to perform testing in actual proposed packaged and used conditions. Vishay optoelectronics die products are tested using Vishay optoelectronics based quality assurance procedures and are manufactured using Vishay optoelectronics established processes. Estimates such as those described and set forth in this datasheet for semiconductor die will vary depending on a number of packaging, handling, use, and other factors. Therefore sold die may not perform on an equivalent basis to standard package products.

PRODUCT SUMMARY				
COMPONENT	I _{ra} (μΑ)	φ (deg)	λ _{0.1} (nm)	
T1120P	35	± 60	430 to 1100	

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION				
ORDERING CODE PACKAGING REMARKS PACKAGE FORM				
T1120P-SD-F	Wafer sawn on foil with discoframe	MOQ: 25 000 pcs	Chip	

Note

· MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V _R	60	V
Junction temperature		T _j	100	°C
Operating temperature range		T _{amb}	- 40 to + 100	°C
Storage temperature range		T _{stg1}	- 40 to + 100	°C
Storage temperature range on foil		T _{stq2}	- 40 to + 50	°C

Document Number: 81121 Rev. 1.3, 23-Mar-11

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BASIC CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Breakdown voltage	I _R = 100 μA, E = 0	V _(BR)		60		V
Forward voltage	I _F = 50 mA V _F 1		1	1.3	V	
Reverse dark current	$V_{\rm B} = 10 \text{ V}, \text{ E} = 0$ $I_{\rm ro}$ 2		2	5	nA	
Diode capacitance	V _R = 0 V, f = 1 MHz, E = 0	C _D		48		pF
	V _R = 3 V, f = 1 MHz, E = 0	C _D		17		pF
Open circuit voltage	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	V _{OC}		350		mV
Temperature coefficient of V _{OC}	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	TK _{VOC}		- 2.6		mV/K
Short circuit current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	I _k		32		μA
Temperature coefficient of I _k	$E_{e} = 1 \text{ mW/cm}^{2}, \lambda = 950 \text{ nm}$	TK _{lk}		0.1		%/K
Reverse light current	E_e = 1 mW/cm ² , λ = 950 nm, V_R = 5 V	I _{ra}	25	35		μΑ
Angle of half sensitivity		φ		± 60		deg
Wavelength of peak sensitivity		λ_{p}		940		nm
Range of spectral bandwidth		λ _{0.1}		430 to 1100		nm
Noise equivalent power	$V_R = 10 \text{ V}, \lambda = 950 \text{ nm}$	NEP		4 x 10 ⁻¹⁴		W/√Hz
Rise time	V_R = 10 V, R_L = 1 k Ω , λ = 820 nm	t _r		100		ns
Fall time	V_R = 10 V, R_L = 1 k Ω , λ = 820 nm	t _f		100		ns

Notes

BASIC CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

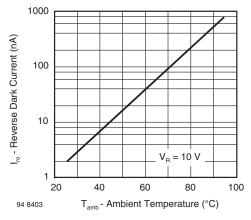


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

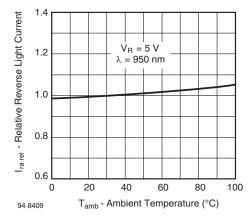


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature

[·] The measurements are based on samples of die which are mounted on a TO-header without resin coating

Vishay Semiconductors

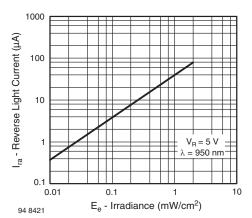


Fig. 3 - Reverse Light Current vs. Irradiance

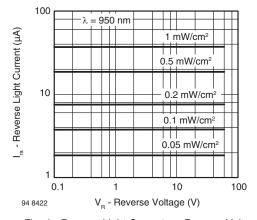


Fig. 4 - Reverse Light Current vs. Reverse Voltage

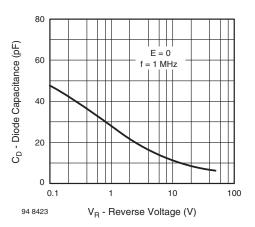


Fig. 5 - Diode Capacitance vs. Reverse Voltage

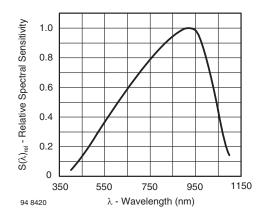


Fig. 6 - Relative Spectral Sensitivity vs. Wavelength

MECHANICAL DIMENSIONS					
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Length of chip edge (x-direction)	L _x		2.37		mm
Length of chip edge (y-direction)	L _y		2.37		mm
Sensitive area	As		4.4		mm ²
Die height	Н		0.28		mm
Bond pad anode	axb		0.2 x 0.2		mm ²

ADDITIONAL INFORMATION (1)				
Frontside metallization, anode	Aluminum			
Backside metallization, cathode	NiV-Ag			
Dicing	Sawing			
Die bonding technology	Epoxy bonding			

Note

The visual inspection shall be made in accordance with the "specification of visual inspection as referenced". The visual inspection of chip backside is performed with stereo microscope with incident light and 40x to 80x magnification.

The quality inspection (final visual inspection) is performed by production. An additional visual inspection step as special release procedure by QM is not installed.

⁽¹⁾ All chips are checked in accordance with the Vishay Semiconductor, specification of visual inspection FVOV6870.

T1120P

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HANDLING AND STORAGE CONDITIONS

- The hermetically sealed shipment lots shall be opened in temperature and moisture controlled cleanroom environment only. It is mandatory to follow the rules for disposition of material that can be hazardous for humans and environment.
- Product must be handled only at ESD safe workstations. Standard ESD precautions and safe work environments are as defined in MIL-HDBK-263.
- Singulated die are not to be handled with tweezers. A vacuum wand with non metallic ESD protected tip should be used.

PACKING

Chips are fixed on adhesive foil. Upon request the foils can be mounted on plastic frame or disco frame. For shipment, the wafers are arranged to stacks and hermetically sealed in plastic bags to ensure protection against environmental influence (humidity and contamination).

Use for recycling reliable operators only. We can help getting in touch with your nearest sales office. By agreement we will take back packing material, if it is sorted. You will have to bear the costs of transport. We will invoice you for any costs incurred for packing material that is returned unsorted or which we are not obliged to accept.



Legal Disclaimer Notice

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Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.